



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

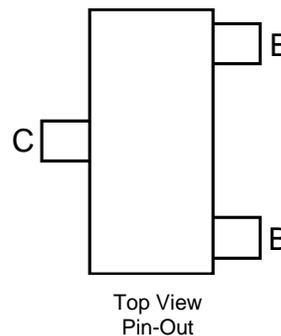
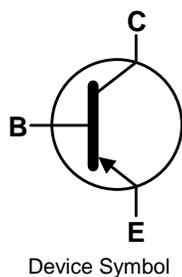
- $BV_{CEO} > -40V$
- $I_C = -2A$ high Continuous Collector Current
- $I_{CM} = -3A$ Peak Pulse Current
- Low Saturation Voltage -225mV Max @ $I_C = -1A$.
- $R_{CE(SAT)} = 90m\Omega$ at 0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Complimentary NPN Type: NK-ZXTN4240F

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight 0.008 grams (Approximate)

Application

- Gate Driving MOSFETs and IGBTs
- Load Switch
- DC-DC Converters
- Battery Charging



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Collector Current	I _{CM}	-3	A
Continuous Collector Current	I _C	-2	A
Base Current	I _B	-300	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

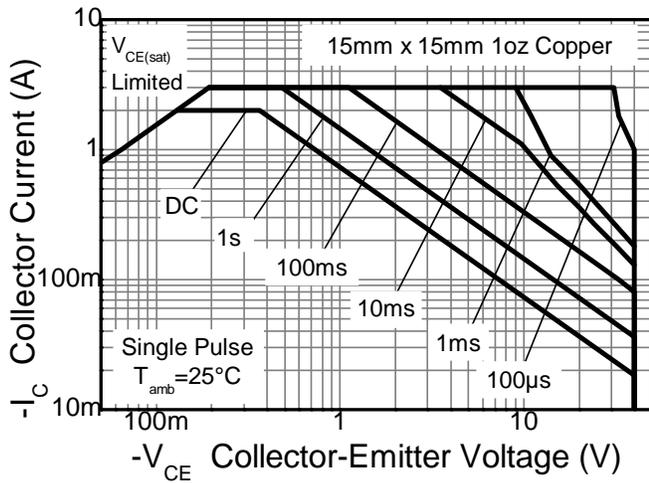
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	730	mW
Power Dissipation (Note 6)	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	R _{θJA}	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 6)	R _{θJA}	209	°C/W
Thermal Resistance, Junction to Lead (Note 7)	R _{θJL}	75	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

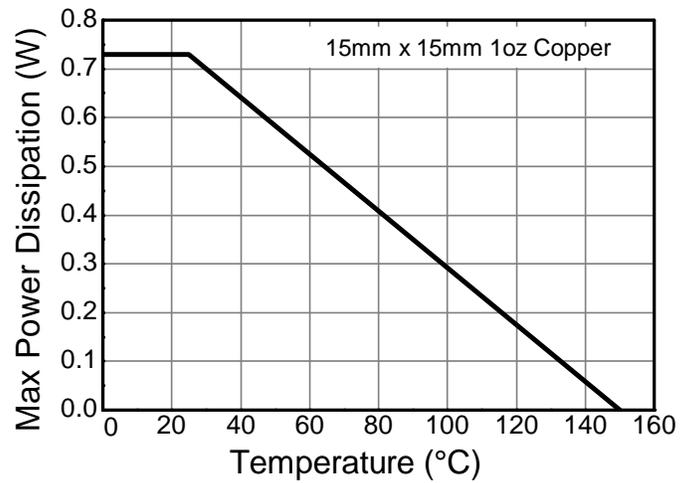
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Same as note (5), except the device is mounted on minimum recommended pad layout.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

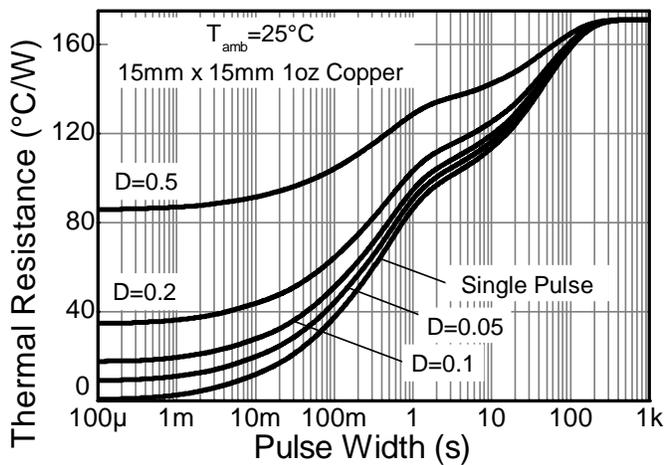
Thermal Characteristics and Derating Information



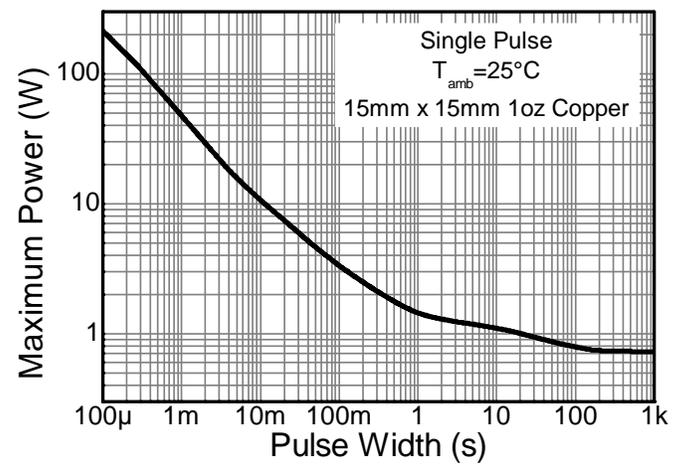
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	—	V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	-40	—	—	V	$I_C = -10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	—	V	$I_E = -100\mu\text{A}$
Collector-Base Cutoff Current	I_{CBO}	—	—	-100	nA	$V_{CB} = -30\text{V}, I_E = 0$
		—	—	-50	μA	$V_{CB} = -30\text{V}, I_E = 0, T_A = +150^\circ\text{C}$
Emitter-Base Cutoff Current	I_{EBO}	—	—	-100	nA	$V_{EB} = -4\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 9)						
DC Current Gain	h_{FE}	300	—	—	—	$V_{CE} = -2\text{V}, I_C = -0.1\text{A}$
		260	—	—		$V_{CE} = -2\text{V}, I_C = -0.5\text{A}$
		210	—	—		$V_{CE} = -2\text{V}, I_C = -1\text{A}$
		100	—	—		$V_{CE} = -2\text{V}, I_C = -2\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	-100	mV	$I_C = -100\text{mA}, I_B = -1\text{mA}$
		—	-45	-110		$I_C = -500\text{mA}, I_B = -50\text{mA}$
		—	—	-225		$I_C = -750\text{mA}, I_B = -15\text{mA}$
		—	—	-225		$I_C = -1\text{A}, I_B = -50\text{mA}$
		—	—	-350		$I_C = -2\text{A}, I_B = -200\text{mA}$
Equivalent On-Resistance	$R_{CE(SAT)}$	—	90	220	m Ω	$I_C = -500\text{mA}, I_B = -50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	-1.1	V	$I_C = -2\text{A}, I_B = -200\text{mA}$
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	—	—	-0.75	V	$V_{CE} = -2\text{V}, I_C = -100\text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Switching times	t_D	—	21	—	ns	$V_{CC} = -10\text{V}, I_C = -500\text{mA}, I_{B1} = I_{B2} = -50\text{mA}$
	t_R	—	22	—		
	t_S	—	120	—		
	t_F	—	23	—		
Transition Frequency	f_T	100	—	—	MHz	$V_{CE} = -10\text{V}, I_C = -100\text{mA}, f = 100\text{MHz}$
Output Capacitance	C_{OB}	—	—	28	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$

 Note: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

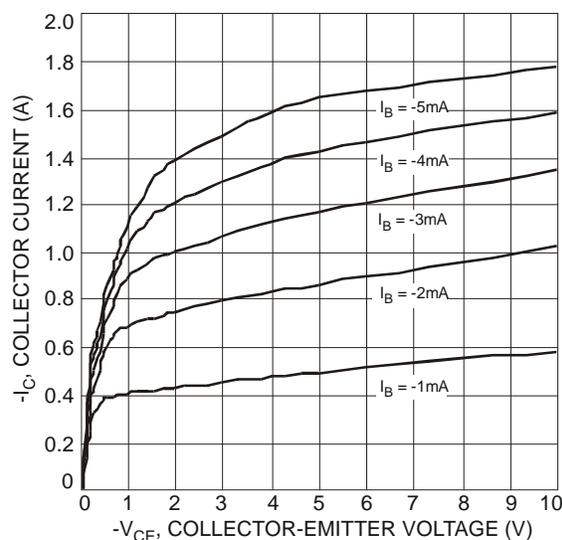
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)


Figure 1 Typical Collector Current vs. Collector-Emitter Voltage

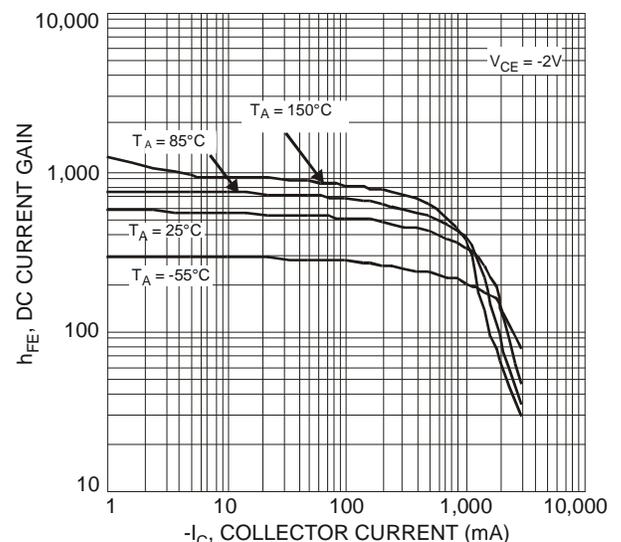


Figure 2 Typical DC Current Gain vs. Collector Current

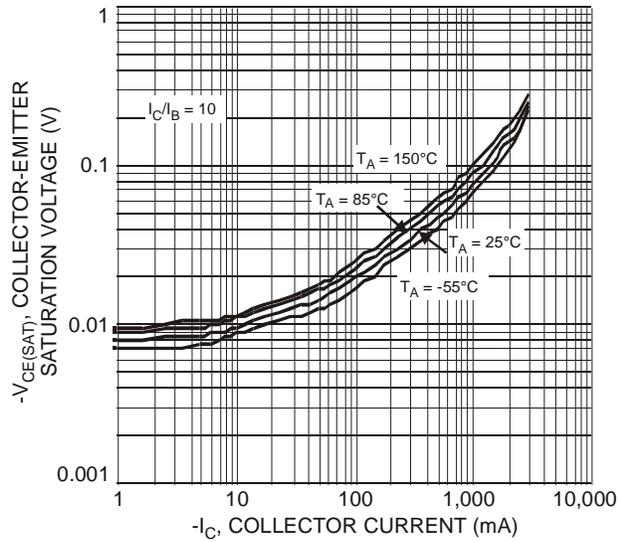


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

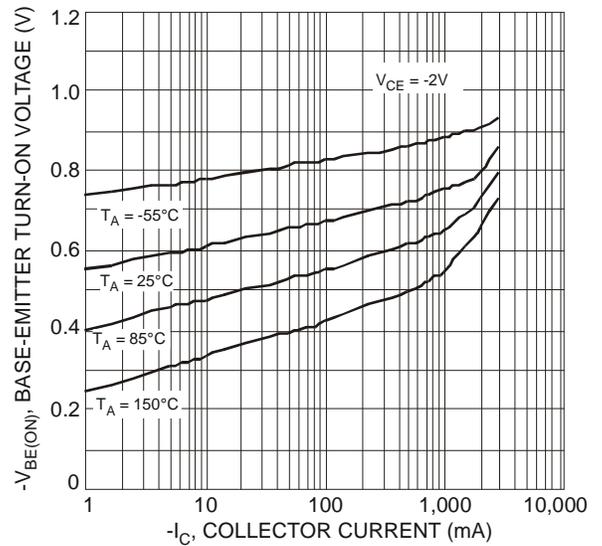


Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

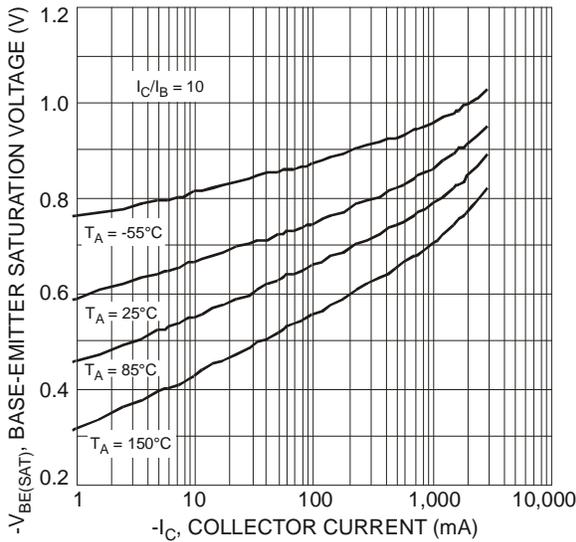


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

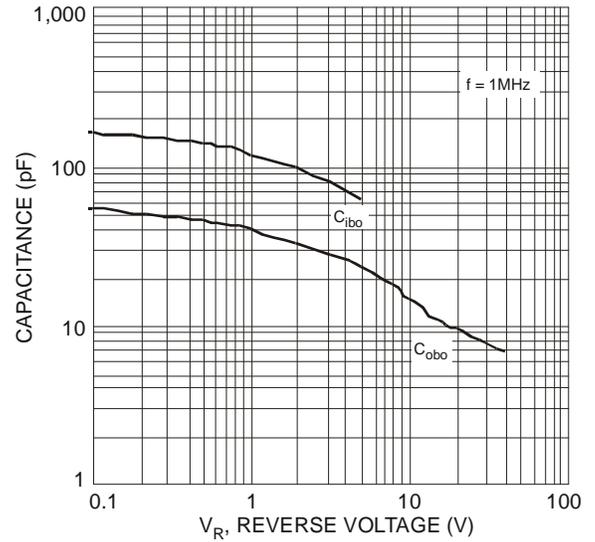


Figure 6 Typical Capacitance Characteristics

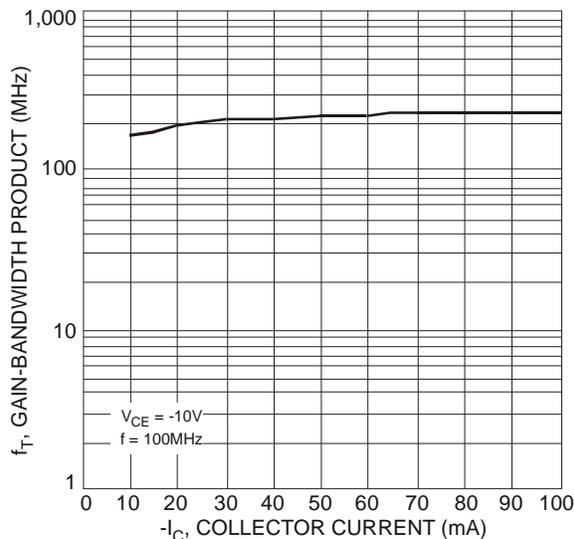
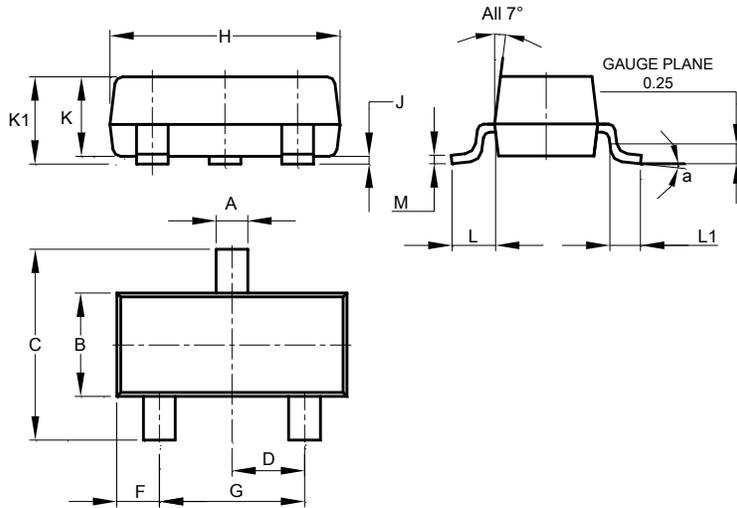


Figure 7 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions

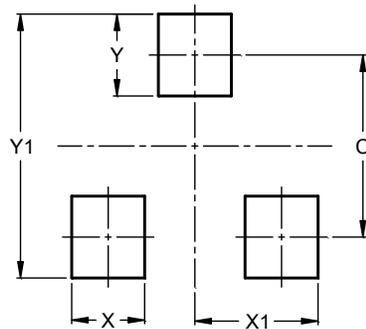
SOT23



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9